## NSN 5962-01-269-1007

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Body Length:
0.840 inches
Body Width:
Between 0.220 inches and 0.310 inches
Body Height:
0.140 inches
Maximum Power Dissipation Rating:
739.0 milliwatts
Operating Tempurature Range: -55.0/+125.0 degrees celsius
-
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Schottky and programmable and bipolar and 3-state output
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
6 input
Case Outline Source And Designator:
D-2 mil-m-38510
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
-0.5 volts power source and 7.0 volts power source
Time Rating Per Chacteristic:
80.00 nanoseconds propagation delay time, low to high level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low level output and 80.00 nanoseconds propagation delay time, high to low leve
output
Memory Device Type:
Rom
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
16 printed circuit
Shelf Life:
N/a
Unit Of Measure:
-
Demilitarization:

Yes - demil/mli

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